

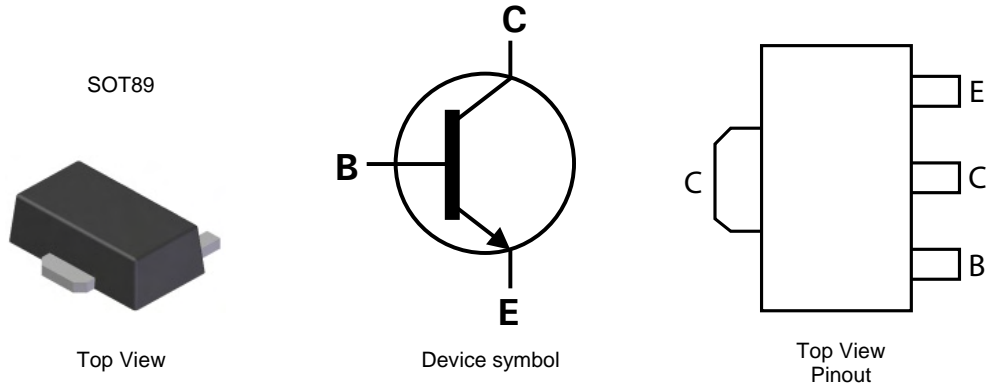
60V LOW $V_{CE(sat)}$ NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT751)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free "Green" Device (Note 2)**

Mechanical Data

- Case: SOT89
- Case material: molded Plastic. "Green" molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (Approximate)

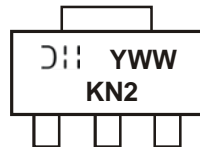


Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT651-13	KN2	13	12	2,500

- Notes:
1. No purposefully added lead.
 2. "Green" devices, Halogen and Antimony Free, Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>
 3. For Packaging Details, go to our website at <http://www.diodes.com>.

Marking Information



KN2 = Product Type Marking Code
 DII = Manufacturer's Marking Code
 YWW = Date Code Marking
 Y = Last digit of year (ex: 7 = 2007)
 WW = Week code (01 – 53)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3	A
Peak Pulse Collector Current	I_{CM}	6	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 4)	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	18.2	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 5)						
Collector-Base Breakdown Voltage	BV_{CBO}	80	—	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	60	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector-Base Cutoff Current	I_{CBO}	—	—	0.1 10	μA	$V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
Emitter-Base Cutoff Current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 4\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 5)						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	0.08 0.23	0.3 0.6	V	$I_C = 1\text{A}, I_B = 100\text{mA}$ $I_C = 3\text{A}, I_B = 300\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	0.85	1.25	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	—	0.8	1	V	$V_{CE} = 2\text{V}, I_C = 1\text{A}$
DC Current Gain	h_{FE}	70 100 80 40	200 200 185 120	— 300 — —	—	$V_{CE} = 2\text{V}, I_C = 50\text{mA}$ $V_{CE} = 2\text{V}, I_C = 500\text{mA}$ $V_{CE} = 2\text{V}, I_C = 1\text{A}$ $V_{CE} = 2\text{V}, I_C = 2\text{A}$
AC CHARACTERISTICS						
Transition Frequency	f_T	140	200	—	MHz	$V_{CE} = 5\text{V}, I_C = 100\text{mA}, f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	30	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Switching Times	t_{on} t_{off}	— —	35 230	— —	ns ns	$V_{CC} = 10\text{V}, I_C = 500\text{mA}, I_{B1} = I_{B2} = 50\text{mA}$

Notes: 4. Device mounted on FR-4 PCB
5. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.

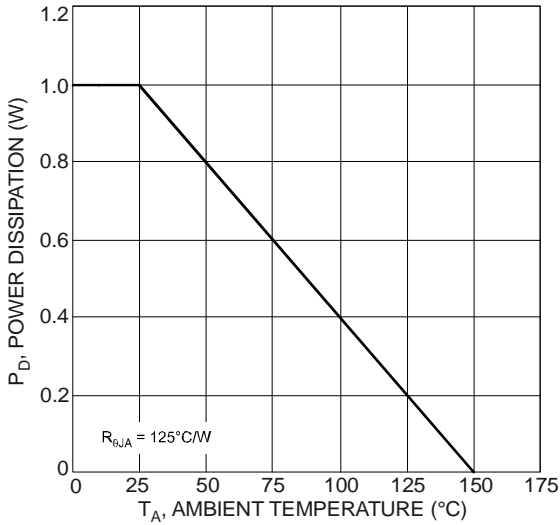


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

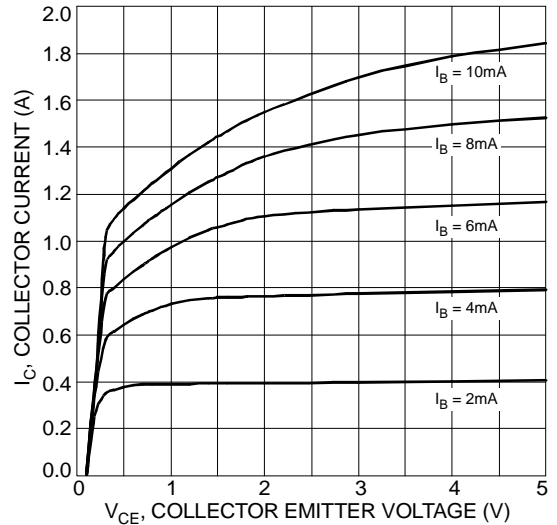


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

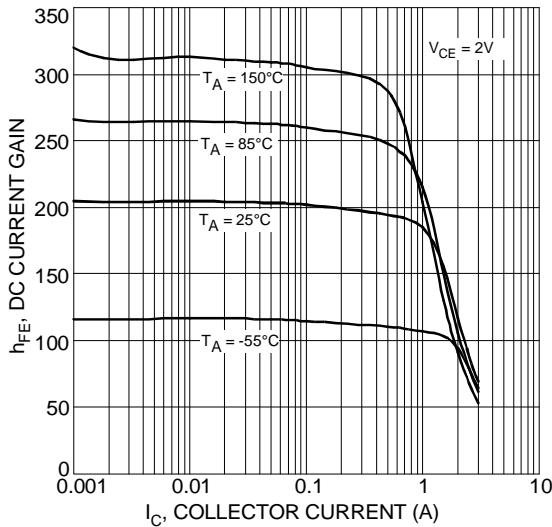


Fig. 3 Typical DC Current Gain vs. Collector Current

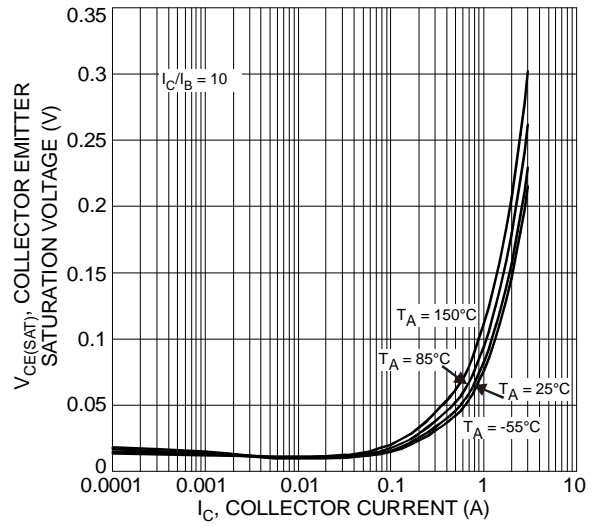


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

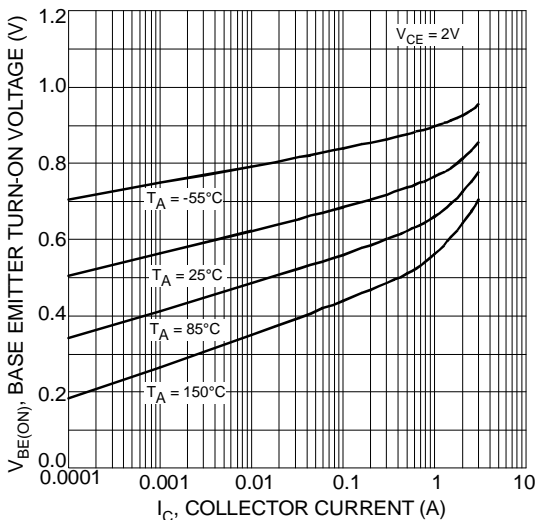


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

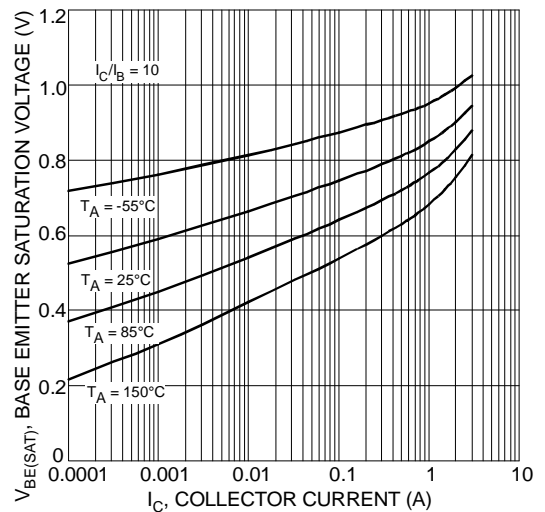


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

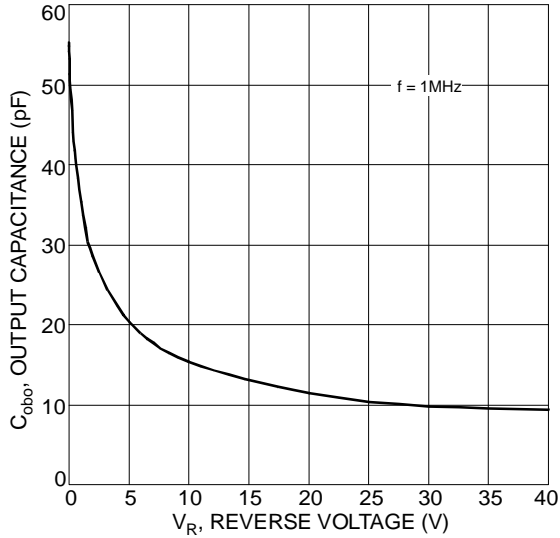


Fig. 7 Typical Output Capacitance Characteristics

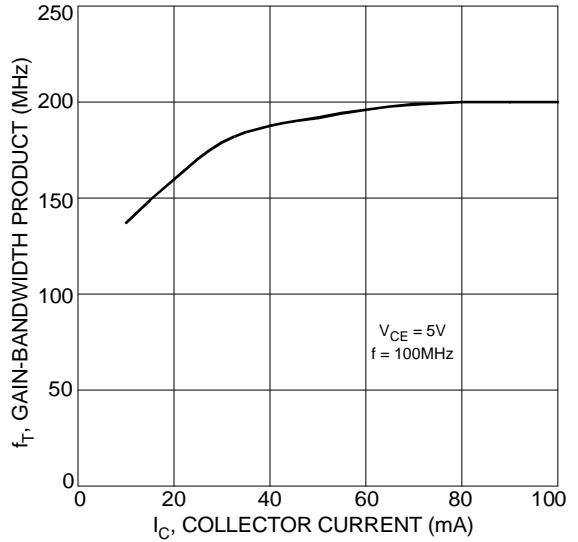
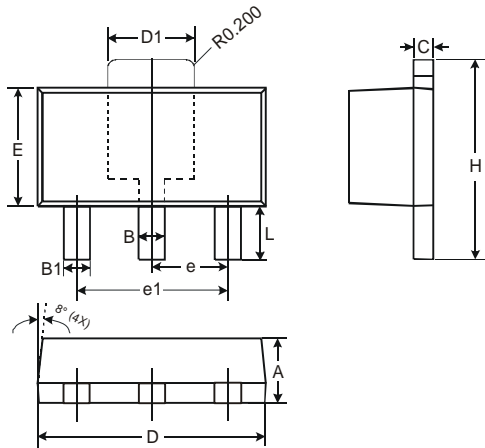


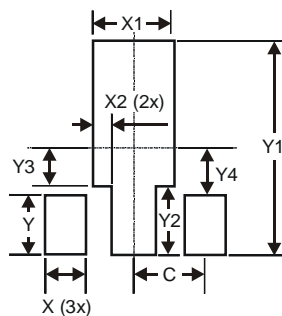
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.43
D	4.40	4.60
D1	1.52	1.83
E	2.29	2.60
e	1.50 Typ	
e1	3.00 Typ	
H	3.94	4.25
L	0.89	1.20
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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